

SEMICONDUCTOR DEVICE, LIQUID CRYSTAL DISPLAY DEVICE, EL DISPLAY DEVICE, SEMICONDUCTOR FILM PRODUCING METHOD, AND SEMICONDUCTOR DEVICE PRODUCING METHOD

Publication number: WO0209192

Publication date: 2002-01-31

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Classification:

- international: H01L21/20; H01L21/336; H01L21/84; H01L27/12; H01L29/786; G02F1/1368; H01L21/02; H01L21/70; H01L27/12; H01L29/66; G02F1/13; (IPC1-7): H01L29/786; G02F1/1368; H01L21/20; H01L21/336

- European: H01L21/77T; H01L21/20D2; H01L21/336D2B; H01L21/336D2C; H01L27/12; H01L29/786A; H01L29/786B4B; H01L29/786E4C2; H01L29/786E4C4

Application number: WO2001JP06365 20010724

Priority number(s): JP20000222275 20000724; JP20000322301 20001023

Also published as:

US6906346 (B2)
 US2004248386 (A1)
 TW515103B (B)

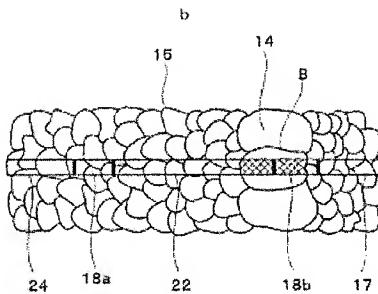
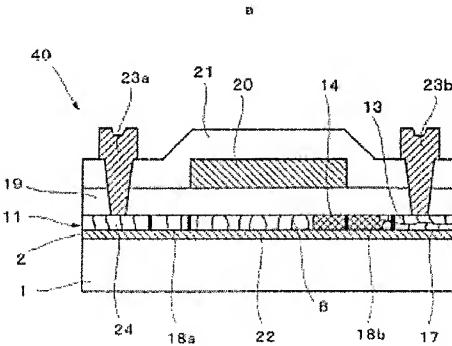
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Abstract of WO0209192

A semiconductor device characterized by comprising a thin film transistor (40) having a multicrystal semiconductor layer (11), the semiconductor layer (11) containing a channel region (22), high-concentration impurity regions (24, 17) positioned on opposite sides of the channel region (22), and low-concentration impurity regions (18a, 18b) positioned between the channel region (22) and the high-concentration impurity regions (24, 17) and having a lower impurity concentration than that of the high-concentration impurity regions (24, 17), wherein the particle size of crystals (14) at least part of which are present in the low-concentration impurity region (18b) is greater than that of other crystals (15).



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